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UNIFORM CONTACT

ABSTRACT OF THE DISCLOSURE

[0037] A semiconductor device can comprise a contact material in substantially continuous contact with a contact region. In an embodiment the contact region may comprise an alloy comprising a wide band-gap material and a low melting point contact material. A wide band-gap material may comprise silicon carbide and a low melting point contact material may comprise aluminum. In another embodiment a substantially uniform ohmic contact may be formed between a contact material and a semiconductor material by annealing the contact at a temperature less than the melting point of the contact material. In an embodiment, the contact may be annealed for more than five hours.

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